# LIXYS

## DSA 30 I 100 PA

#### advanced

V <sub>RRM</sub> =	100 V		
I <sub>FAV</sub> =	30 A		
V <sub>F</sub> =	0.78 V		

## Schottky Diode Gen<sup>2</sup>

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Part number

DSA 30 I 100 PA

### Features / Advantages:

- Very low Vf
- Extremely low switching losses
- low Irm values
- Improved thermal behaviour
- High reliability circuit operation
  Low voltage peaks for reduced protection circuits
- Low noise switching

30 0 1

### **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage
- converters



Backside: cathode

#### Package:

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RRM</sub>	max. repetitive reverse voltage	Τ <sub>ν</sub>	J = 25°C			100	V
I <sub>R</sub>	reverse current	$V_R = 100 V$ $T_v$	, = 25°C			0.9	mA
		V <sub>R</sub> = 100 V T <sub>v</sub>	<sub>/J</sub> = 125°C			5	mA
V <sub>F</sub>	forward voltage	$I_F = 30 A T_V$	,, = 25°C			0.95	V
		$I_{F} = 60 A$				1.15	V
		$I_F = 30 A T_V$	/J = 125°C			0.78	V
		$I_{F} = 60 A$				1.01	V
I <sub>FAV</sub>	average forward current	rectangular d = 0.5 T <sub>c</sub>	c = 150°C			30	Α
V <sub>F0</sub>	threshold voltage	T	<sub>∕J</sub> = 175°C			0.46	V
۲ <sub>F</sub>	slope resistance } for power loss cal	culation only				7.8	mΩ
R <sub>thJC</sub>	thermal resistance junction to case					0.85	K/W
T <sub>vj</sub>	virtual junction temperature			-55		175	°C
P <sub>tot</sub>	total power dissipation	Tc	c = 25°C			175	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine T <sub>v</sub>	<sub>/J</sub> = 45°C			230	Α
C	junction capacitance	$V_{R} = 12 V; f = 1 MHz$ $T_{V}$	, = 25°C		289		pF
E <sub>AS</sub>	non-repetitive avalanche energy	I <sub>AS</sub> = 10 A; L = 100 μH Τ <sub>ν</sub>	<sub>/J</sub> = 25°C			5	mJ
I <sub>AR</sub>	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ.: f = 10 kHz				1	Α



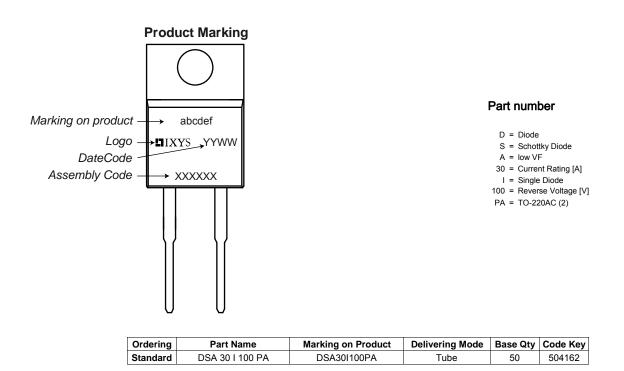
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				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per pin <sup>1)</sup>			35	А	
R <sub>thCH</sub>	thermal resistance case to heatsink			0.50		K/W	
T <sub>stg</sub>	storage temperature		-55		150	°C	
Weight				2		g	
M <sub>D</sub>	mounting torque		0.4		0.8	Nm	
F <sub>c</sub>	mounting force with clip		20		60	Ν	

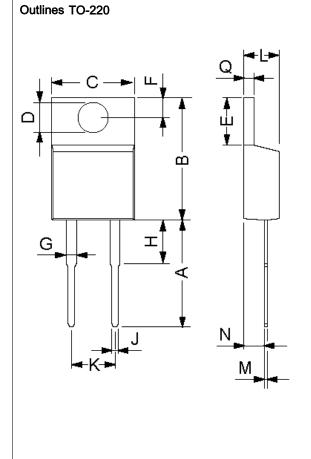
<sup>1)</sup> I<sub>RMS</sub> is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.

In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



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Dim.	Millimeter		Inches		
Dim.	Min.	Max.	Min.	Max.	
А	12.7	14.73	0.5	0.58	
В	14.23	16.51	0.56	0.65	
C	9.66	10.66	0.38	0.42	
D	3.54	4.08	0.139	0.161	
Е	5.85	6.85	2.3	0.42	
F	2.54	3.42	0.1	0.135	
G	1.15	1.77	0.045	0.07	
Н	-	6.35	-	0.25	
J	0.64	0.89	0.025	0.035	
К	4.83	5.33	0.19	0.21	
L	3.56	4.82	0.14	0.19	
М	0.51	0.76	0.02	0.03	
Ν	2.04	2.49	0.08	0.115	
Q	0.64	1.39	0.025	0.055	

IXYS reserves the right to change limits, conditions and dimensions.